

Nanodiamond photocathodes for MPGD based single photon detectors at the future EIC

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On behalf of Trieste, Bari and CERN collaboration

OUTLINE

- > motivation of the R&D
- > Nano diamond (ND): a novel photocathode
- > Setup in Bari: QE measurements
- > Setup at CERN: QE measurements and ageing study
- > THGEM characterization
- > Conclusion



HADRON IDENTIFICATION AT EIC WITH RICH

CHANDRADOY'S
PRESENTATION

Key requirement at EIC > efficient particle identification at high momentum

RICH technique in this environment is challenging:

Compact geometry > short radiator

High rate environment

High momentum > gaseous radiator

Low number
of photons

High space
resolution is
required

Reduce
pad size

Photocathode
must be
robust

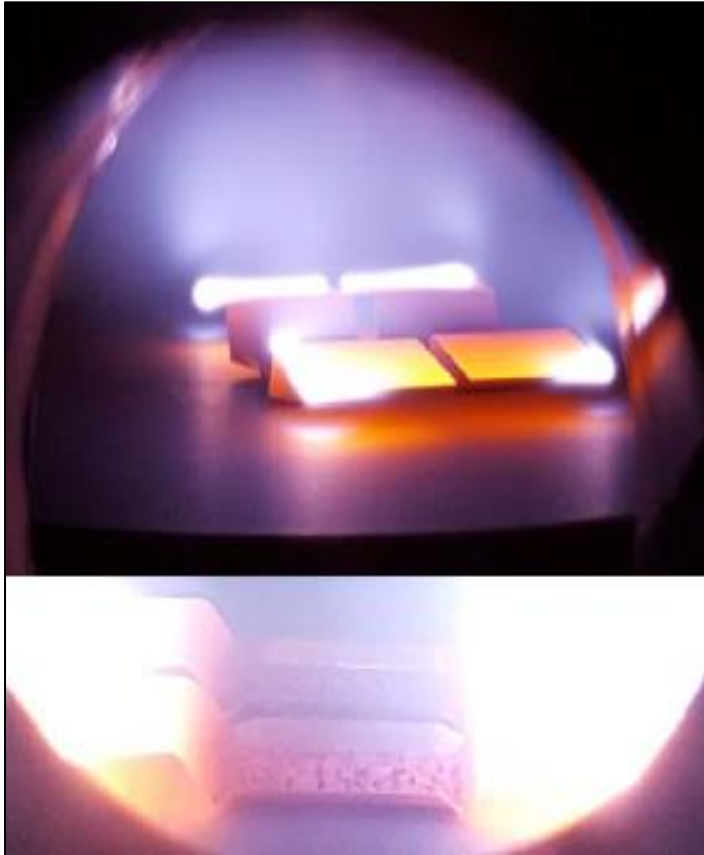
Quest for a
photocathode
alternative to CsI

So far only photocathode in
gaseous detectors

Frank - Tamm >
lower λ

Since fused silica is
opaque for $\lambda < 165$ nm
> Windowless RICH
(gaseous photon detector)

HYDROGENATION AND COATING OF ND



Hydrogenation:

- > Hydrogenation lowers electron affinity (hydrogenation of ND powder)
- > However, hydrogenation with MWPECVD requires high temperature ($> 800^{\circ}\text{C}$)



Coating:

- 1) Preparation a solution (1:1) of H-ND powder with distilled water
- 2) Spraying the solution on the substrate using a pulsed spray technique.
- 3) No of spray shots determine the coating thickness

VUV SENSITIVE PHOTOCATHODES

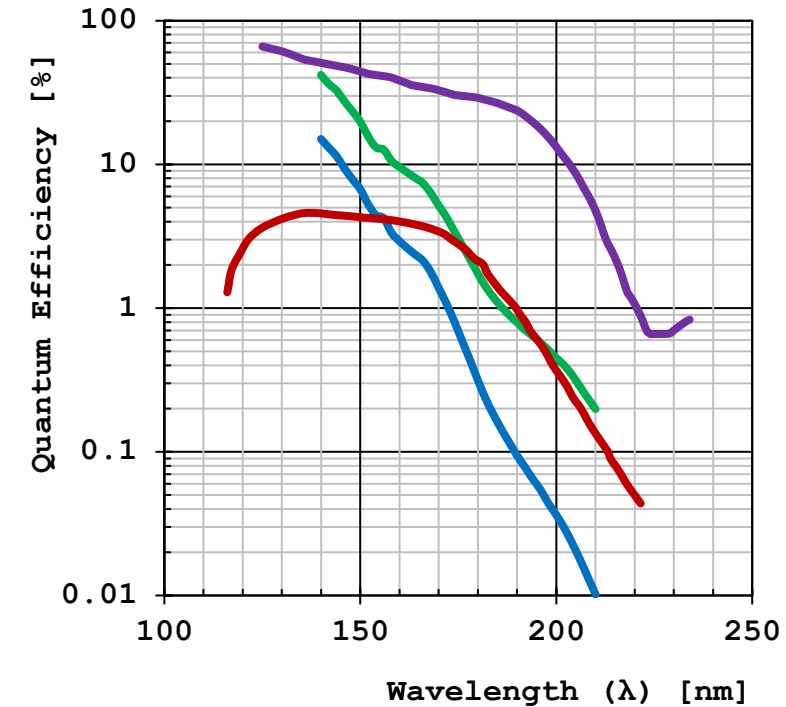
CsI

- > Low electron affinity > 0.1 eV
- > Wide band gap > 6.2 eV
- > Typical Quantum Efficiency > 35 – 50% @ 140 nm
- > CsI has hygroscopic nature
- > Aging > Ion Accumulation > Degradation in QE of PC

Nanodiamond (ND)

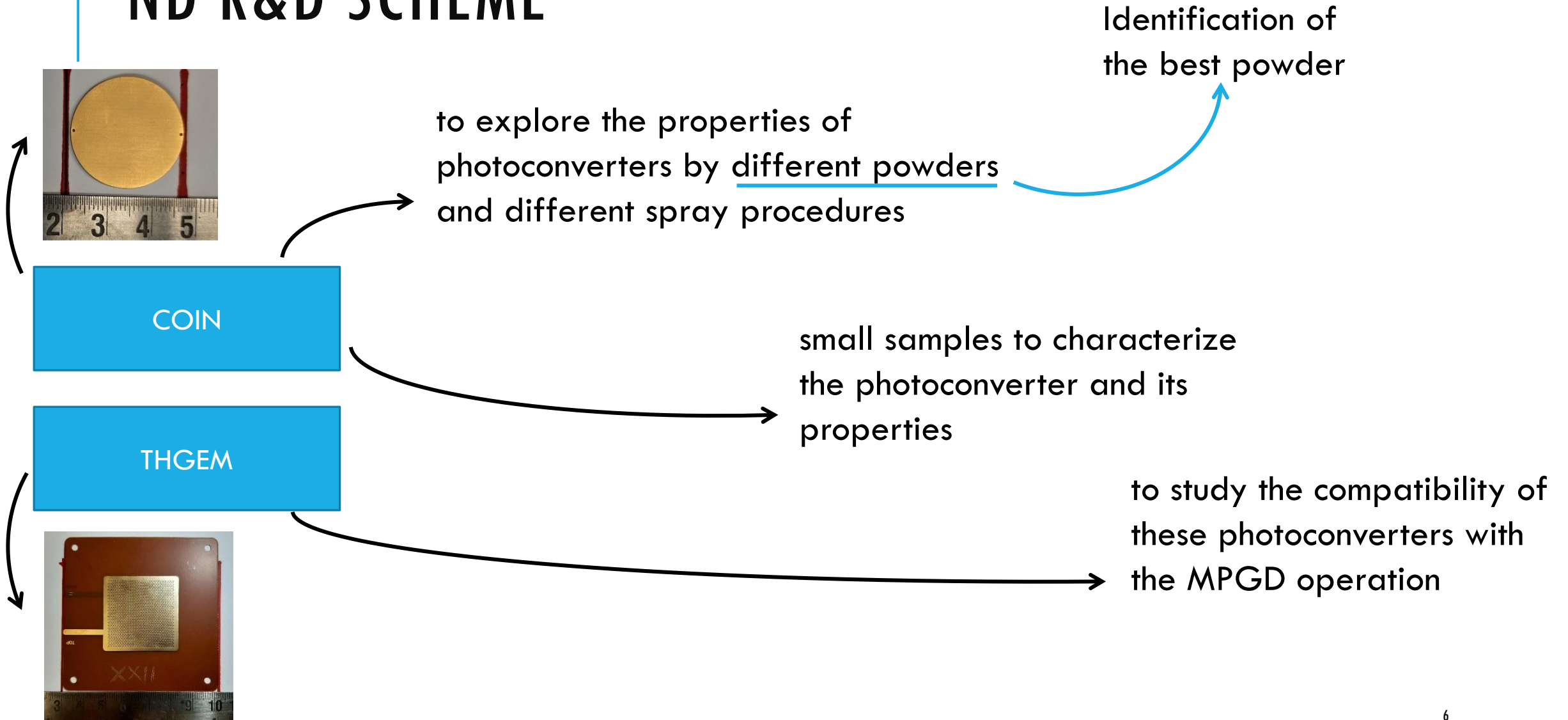
- > Low electron affinity > 0.35 – 0.5 eV
- > Wide band gap > 5.5 eV
- > Preliminary measured QE > 30 – 40% @ 140 nm for Hydrogenated ND. (We meas 7.7% after one year H-ND in H₂O).
- > Chemically inert
- > Radiation hard
- > Good thermal conductivity

Comparison of different Photocathode materials

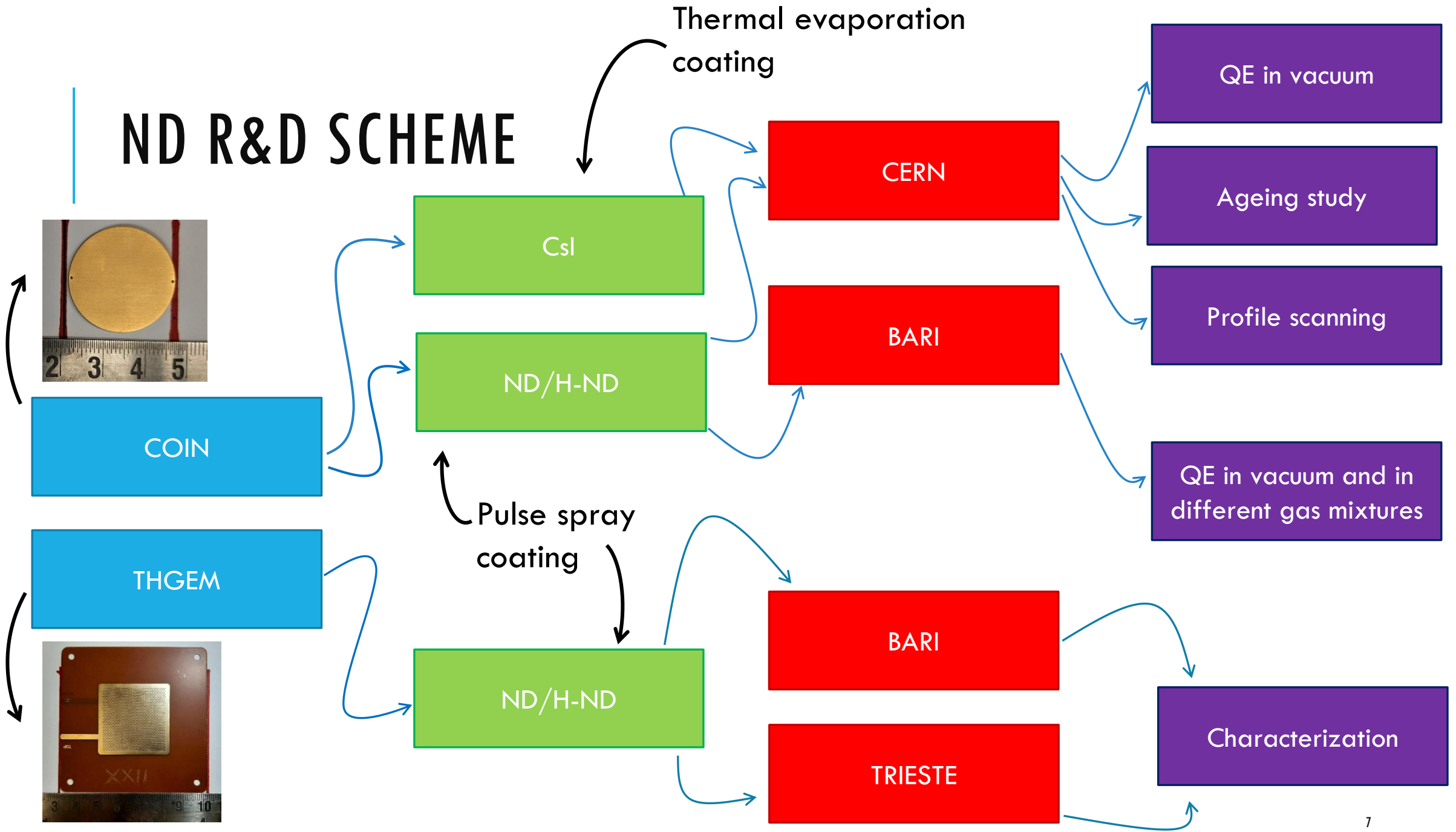


- CsI [NIMA 438 (1999) 94]
- ND [ALP 108 (2016) 083503]
- H-ND [ALP 108 (2016) 083503]
- DNP Hamamatsu Phototube R6800U-26

ND R&D SCHEME



ND R&D SCHEME



Pulsed spray thin film coating setup: No of Shots determine the coating thickness

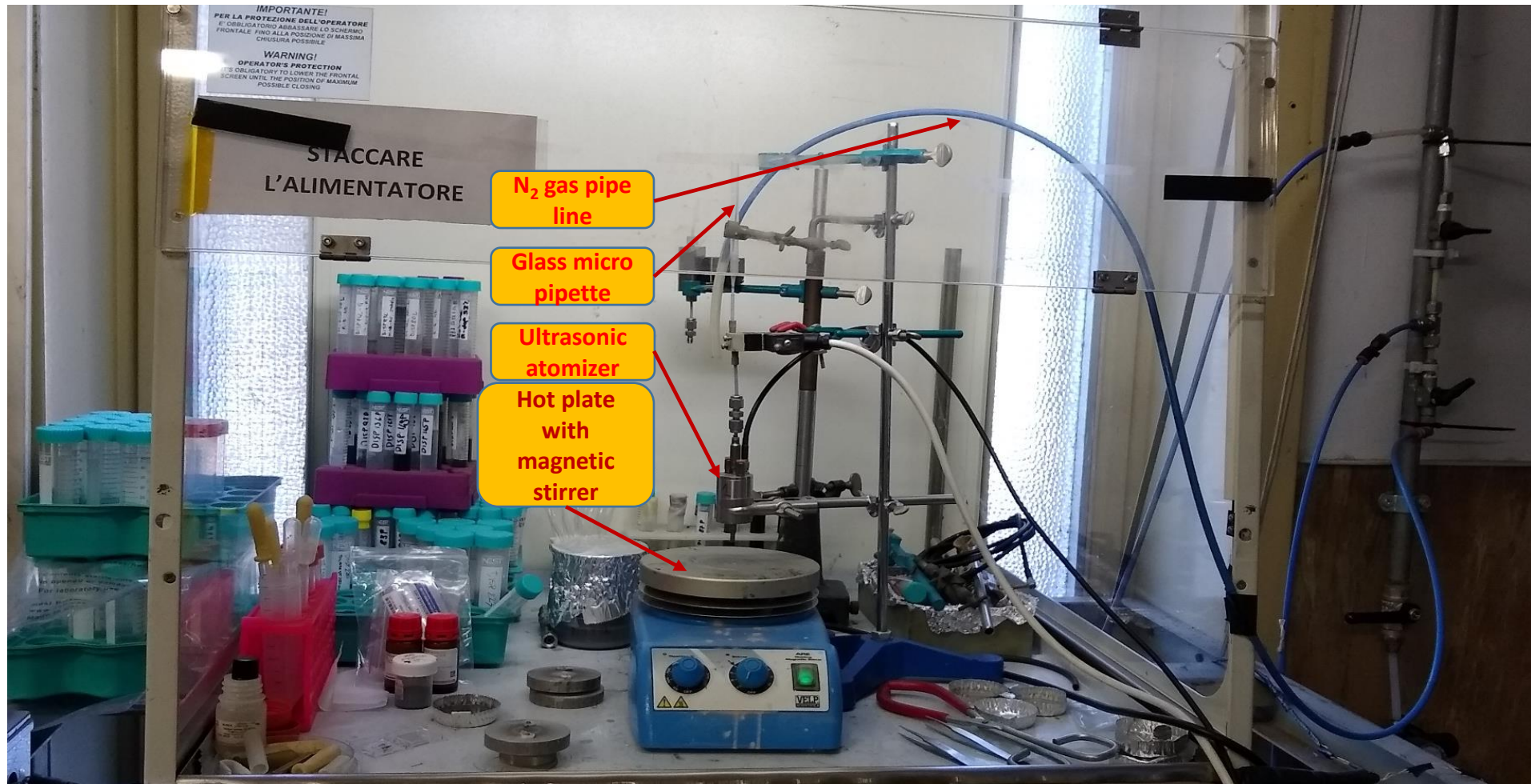


Figure : The pulsed spray technique for thin film coating, equipped with an ultrasonic atomizer and with a heater at INFN Bari, Italy

Pictorial view of photoemission measurement setup:

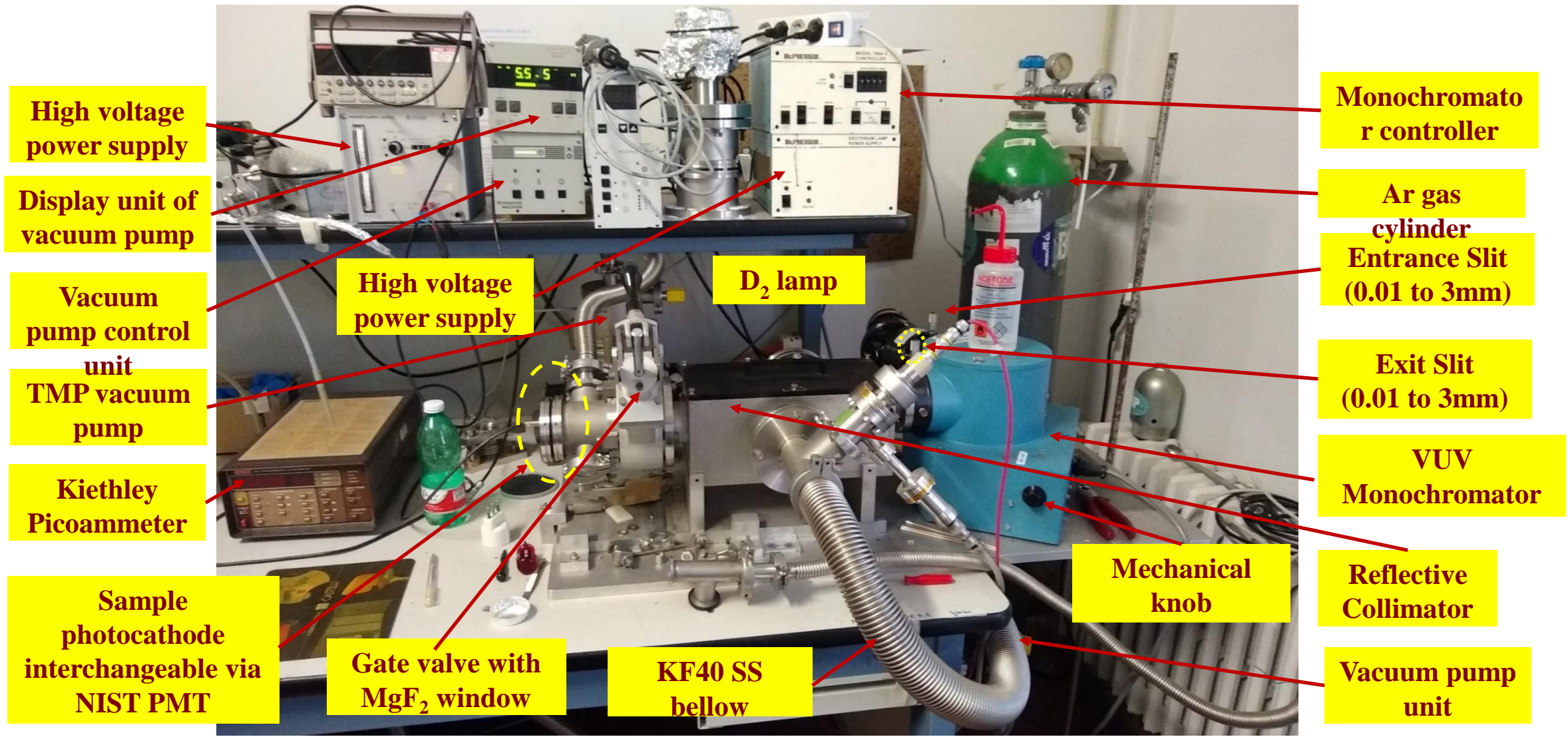


Figure : McPherson VUV monochromator for the photocurrent measurement at INFN Bari, Italy

MEASURING QUANTUM EFFICIENCY IN BARI

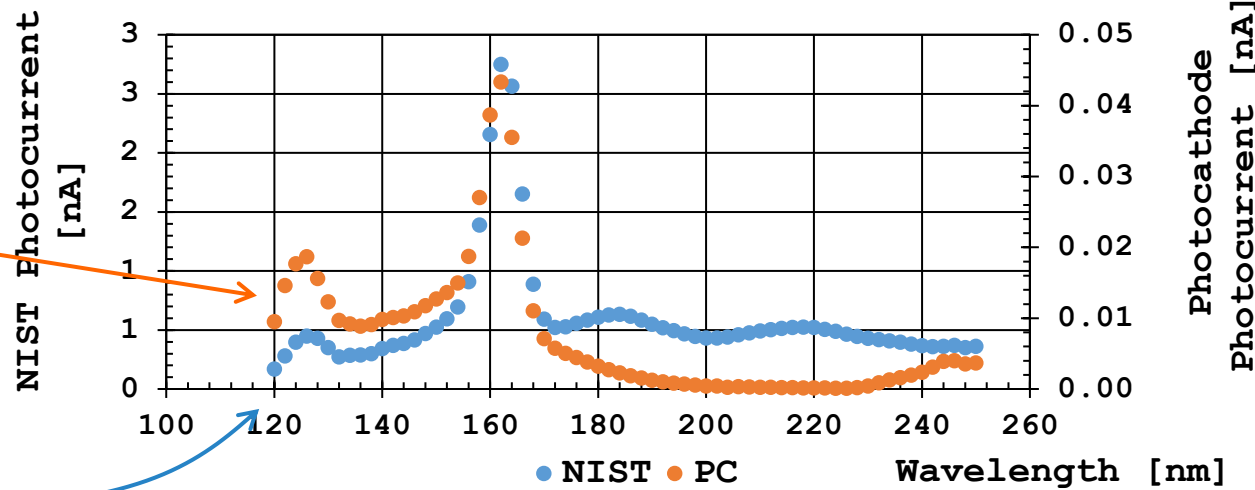
Repeated measurements > results are reproducible

$$Q.E. = \frac{N_e}{N_\gamma}; \quad N_\gamma = \frac{I_{NIST}(\lambda) - I_{NIST}^{dark}}{e} \times \frac{1}{\text{Calibration factor}};$$

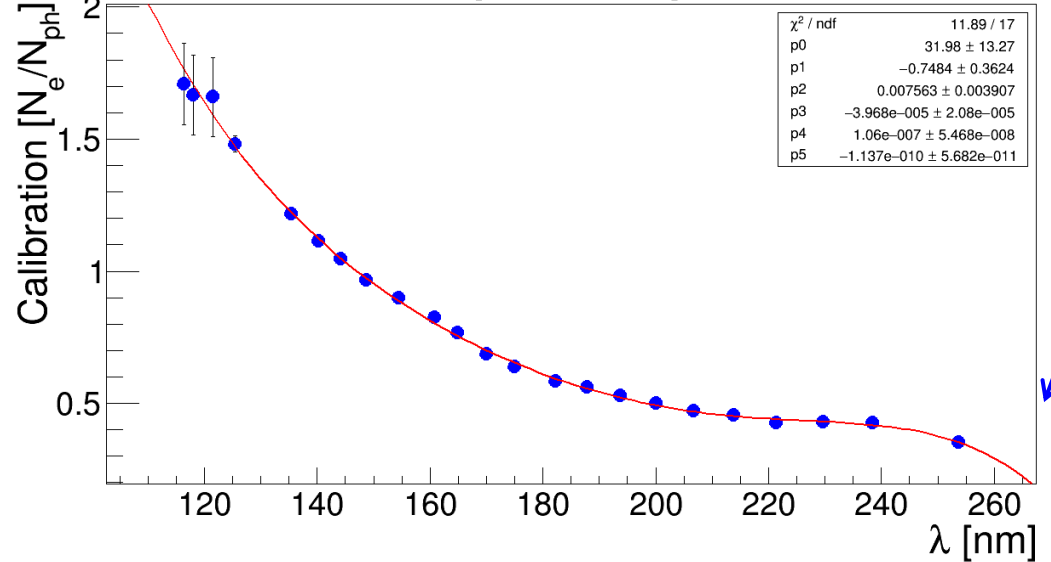
$$N_e = \frac{I_{PC}(\lambda) - I_{PC}^{dark}}{e};$$

$$Q.E. (\lambda) = \frac{I_{PC}(\lambda) - I_{PC}^{dark}}{I_{NIST}(\lambda) - I_{NIST}^{dark}} \times \text{Calibration factor}$$

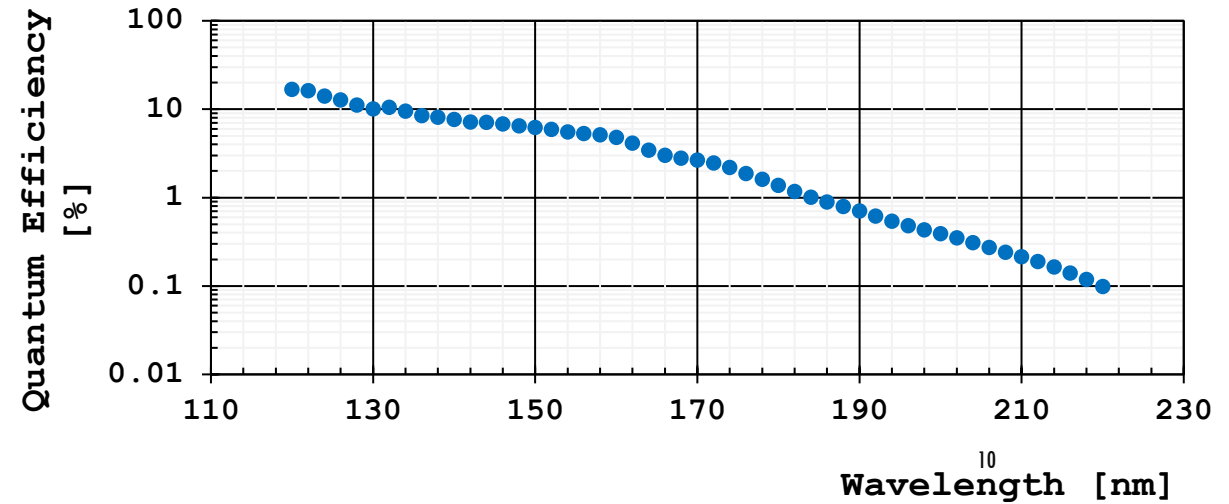
Photocurrent vs. Wavelength scan



NIST Photo-diode [AXUV-100G] calibration curve

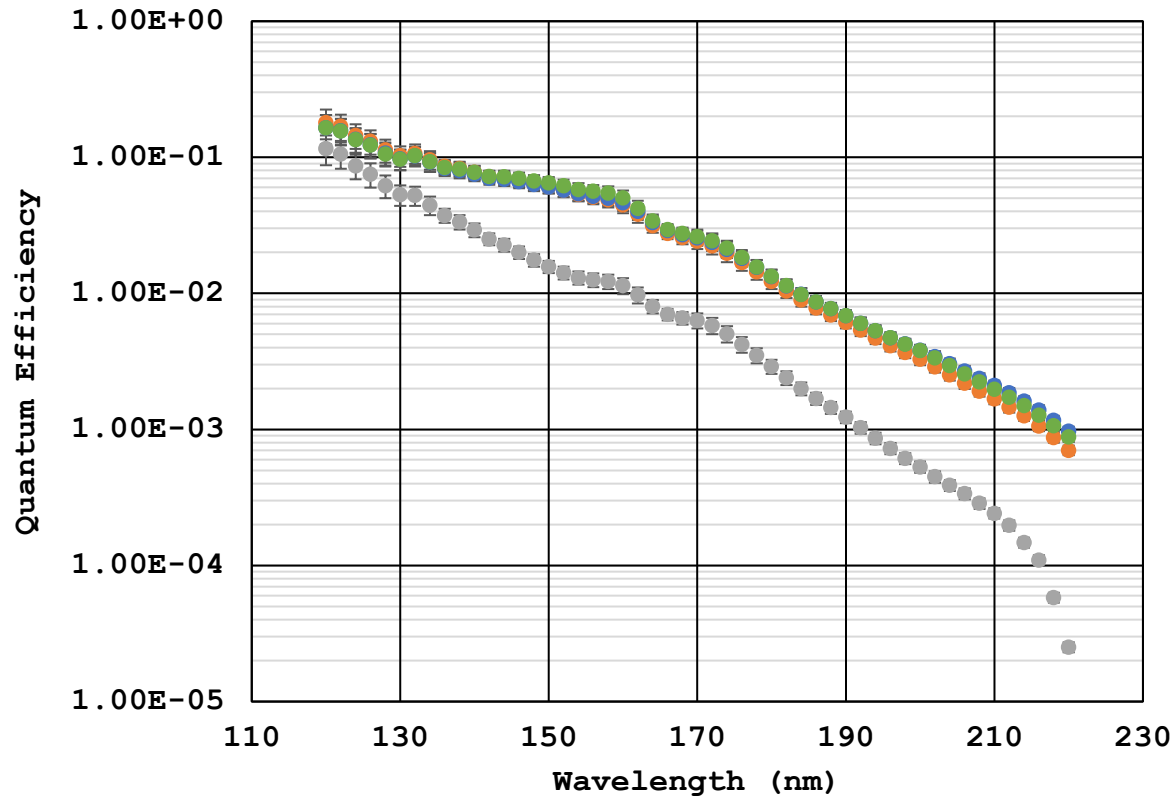


QE: H-ND PCB8 [400 Shots]



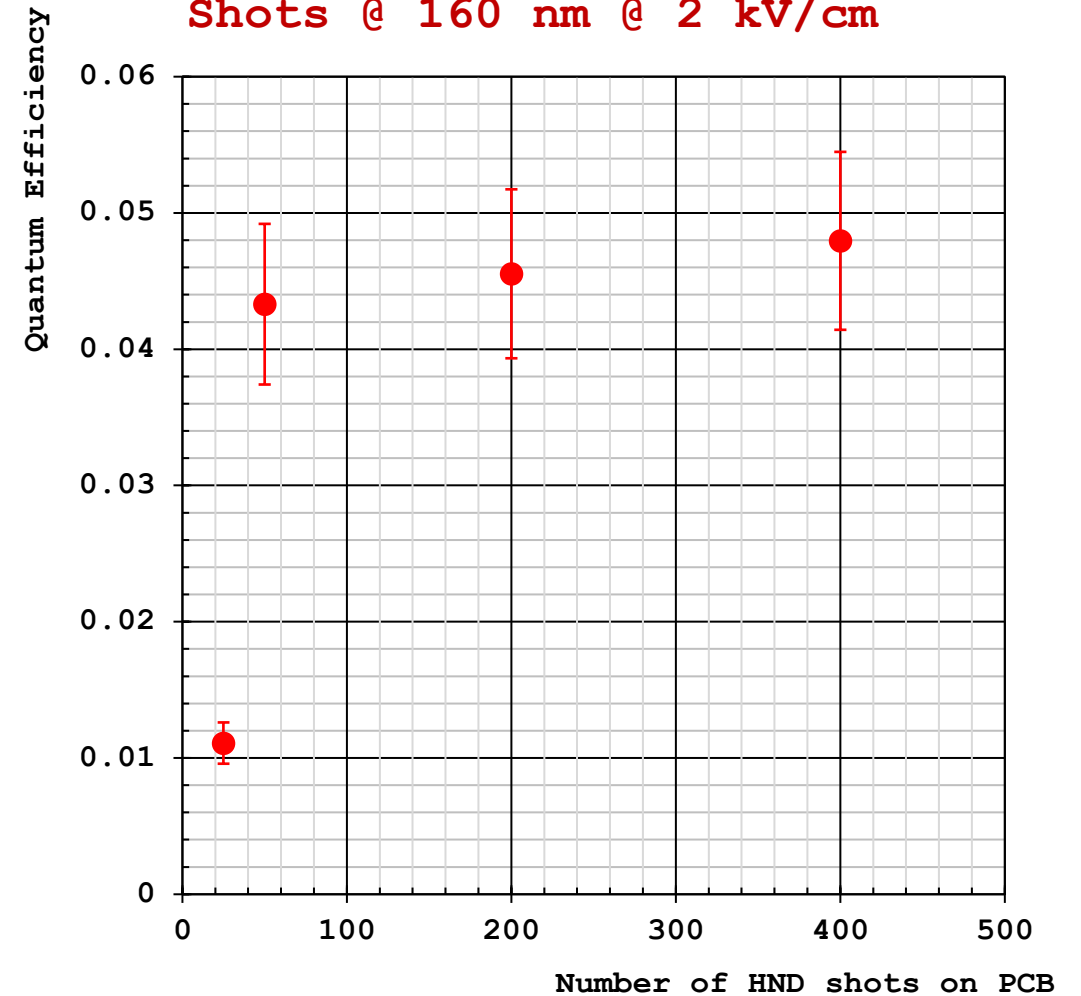
QE vs λ FOR VARIOUS H-ND SHOTS ON PCB COIN

HND_Au_PCB_Coin_Vacuum @ 2 kV/cm



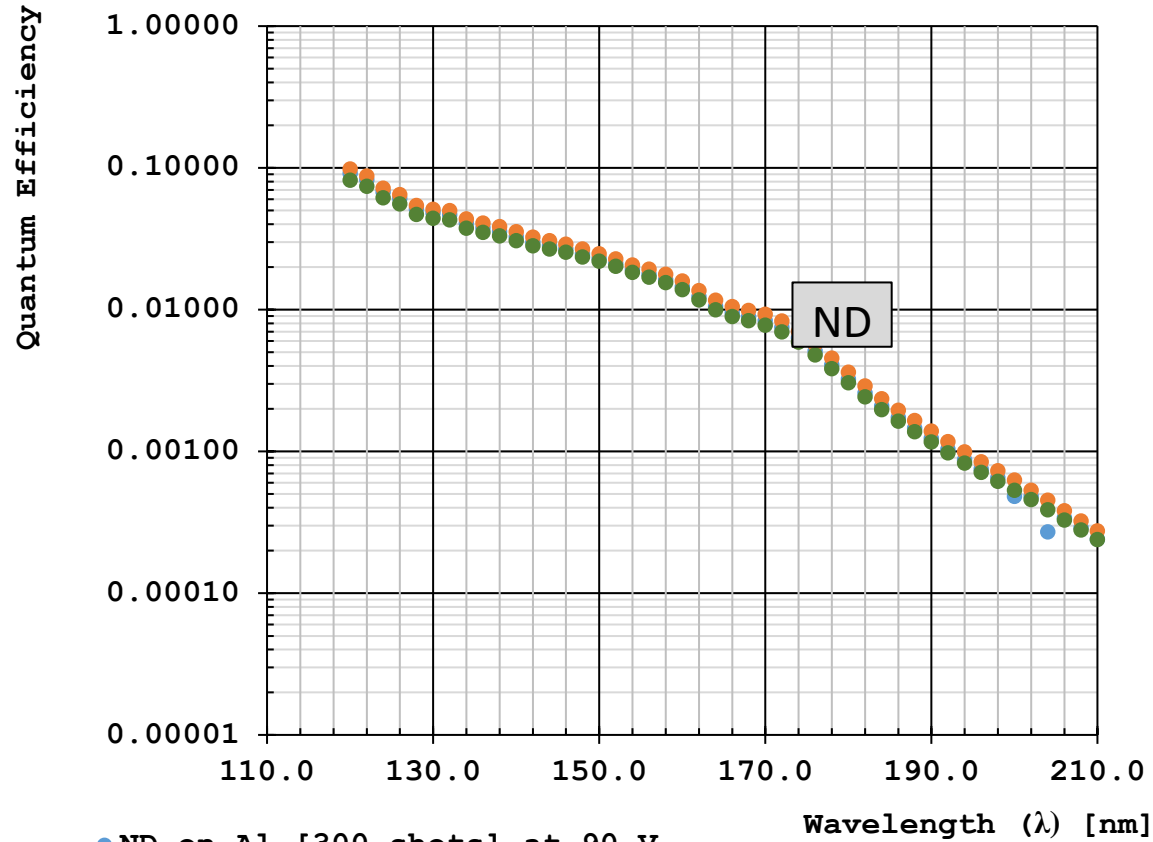
- H-ND on PCB9 [25 Shots] at 500 V
- H-ND on PCB7 [50 Shots] at 500 V
- H-ND on PCB11 [200 Shots] at 500 V
- H-ND on PCB8 [400 Shots] at 500 V

Quantum Efficiency Vs. H-ND Shots @ 160 nm @ 2 kV/cm



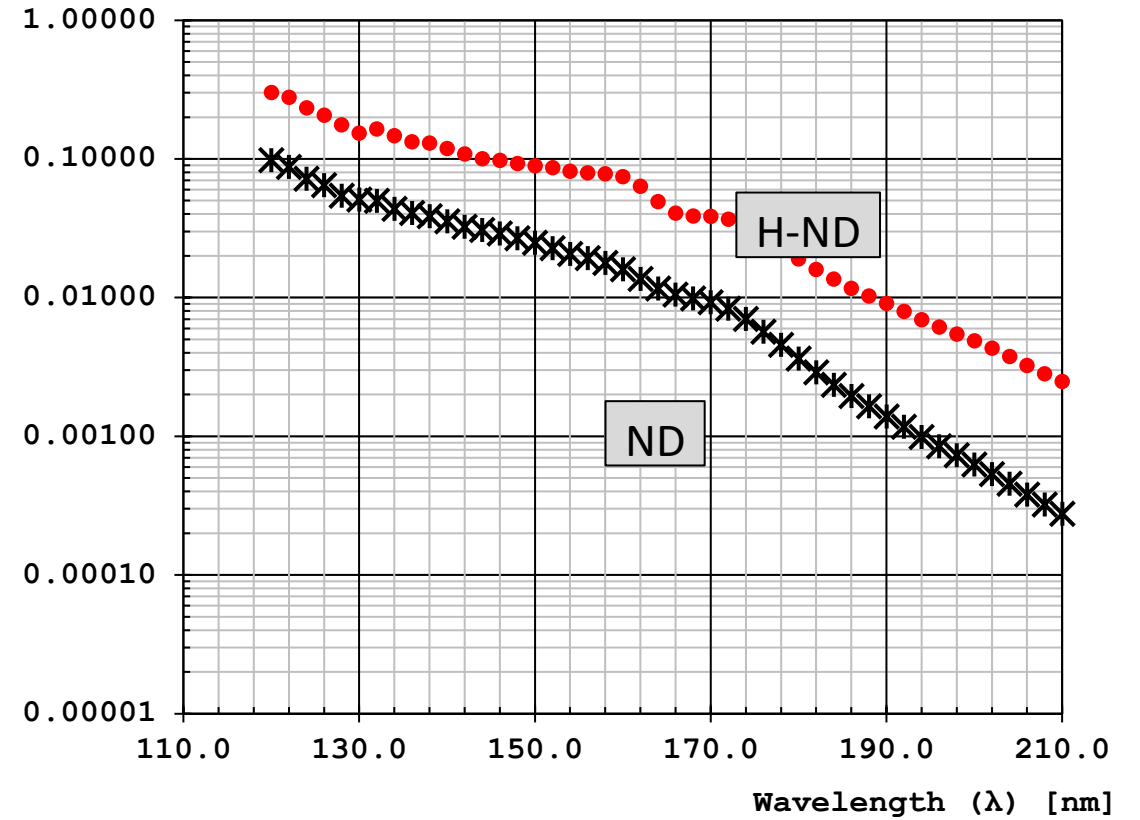
QE OF ND AND H-ND

QE of ND in vacuum



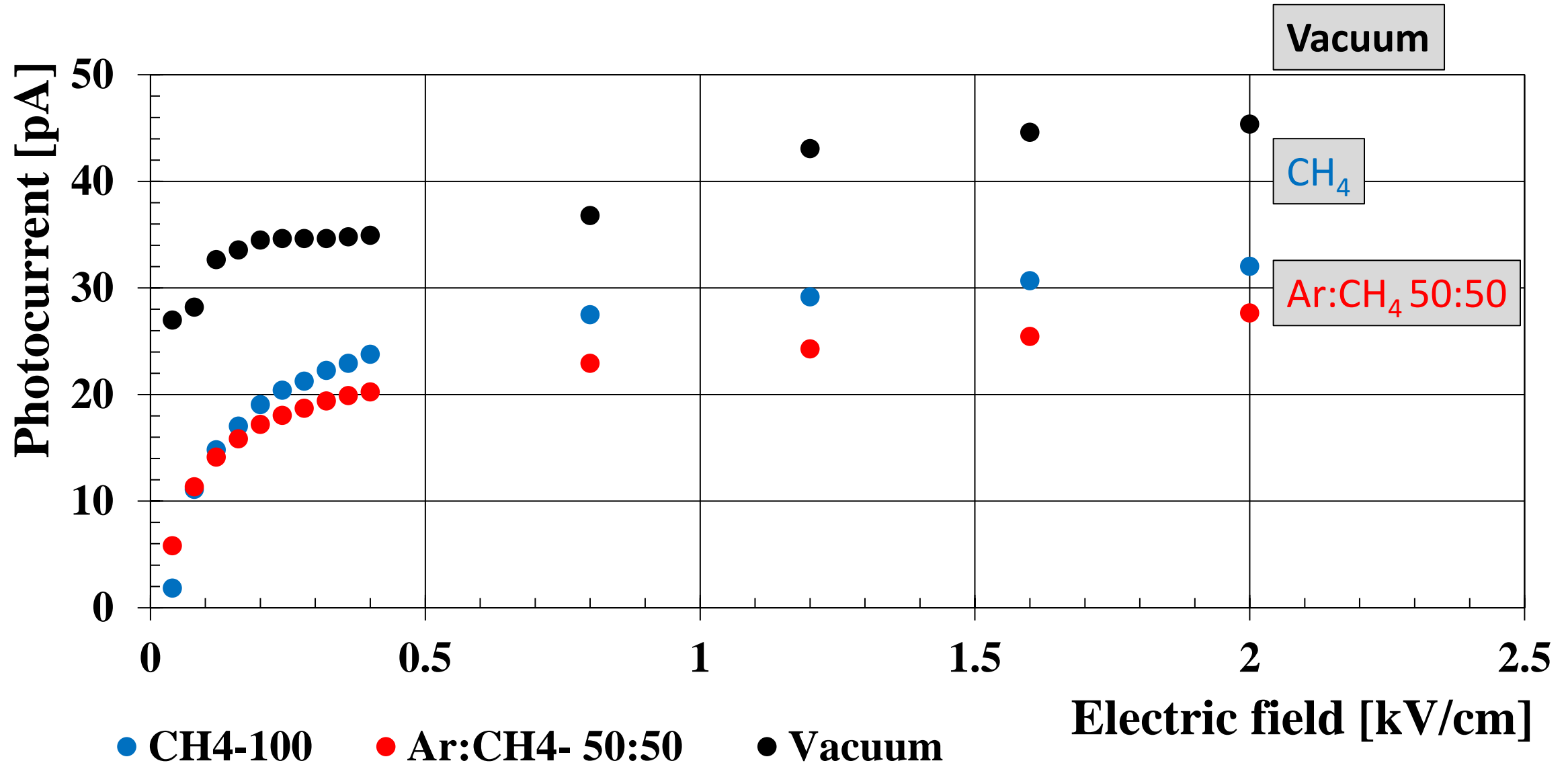
- ND on Al [300 shots] at 90 V
- ND on Al [300 Shots] at 90 V
- ND on Al [300 Shots] at 120 V

Quantum Efficiency vs. Wavelength (λ)

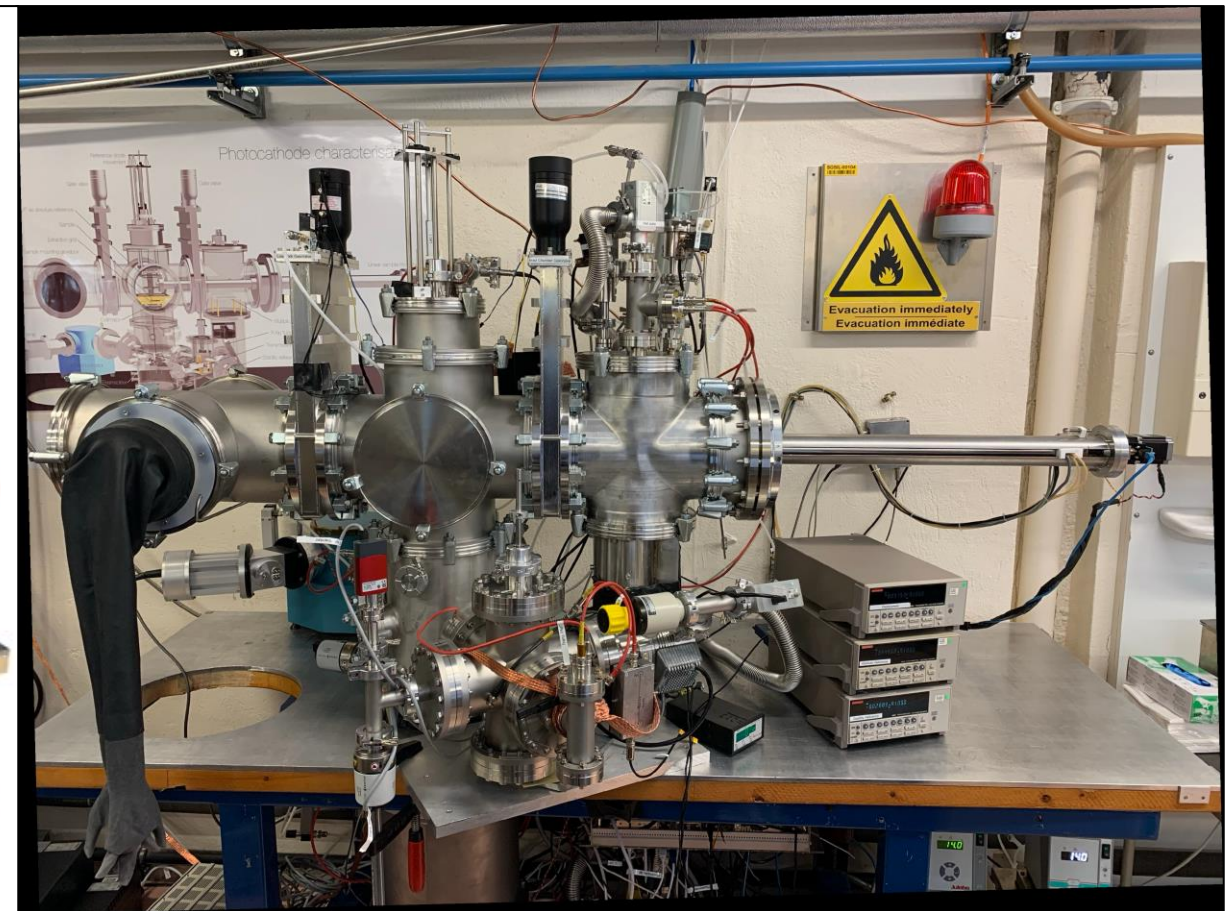
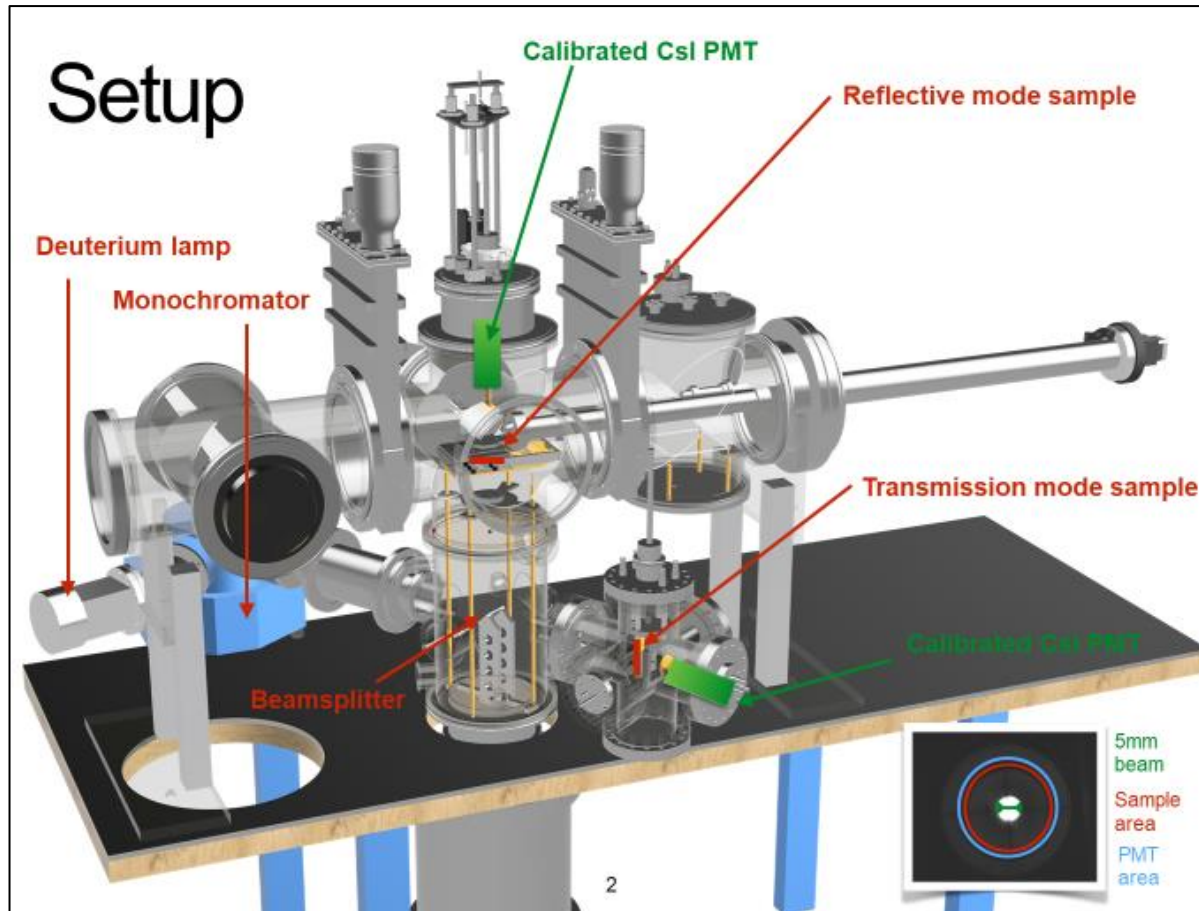


- PCB8 H-ND (400 shots) 500V
- ✕ ND Al Substr [2019]

PHOTOCURRENT vs ELECTRIC FIELD in VACUUM & GAS @ 160 nm



Schematic & Pictorial view of photoemission measurement setup: ASSET



MEASURING QUANTUM EFFICIENCY AT CERN

Repeated measurements > results are reproducible

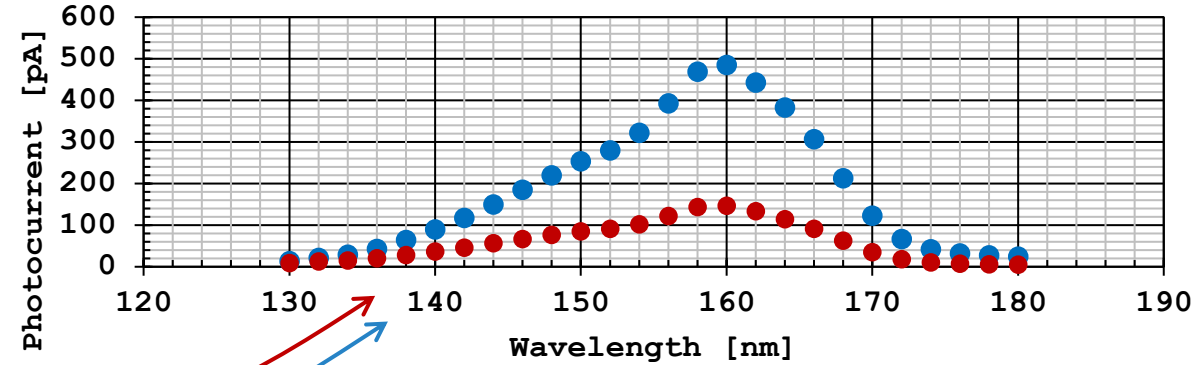
$$QE_{PC}(\lambda) = \frac{N_e}{N_\gamma} = \frac{(I_{PC}/e)}{(factor(\lambda) \times I_{ref(abs)})}$$

$$I_{ref(abs)} = I_{ref} \times \frac{I_{PMT(Top)}}{I_{PMT(Bottom)}}$$

Where $I_{ref} = I_{PMT(Bottom_{withPC})}$

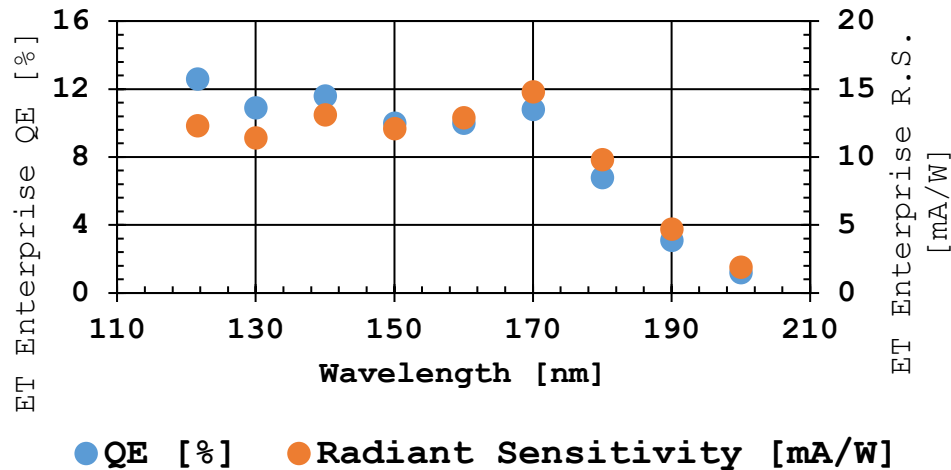
$$factor(\lambda) = \frac{\lambda}{h \times c \times radiant\ sensitivity}$$

Photocurrent vs. wavelength

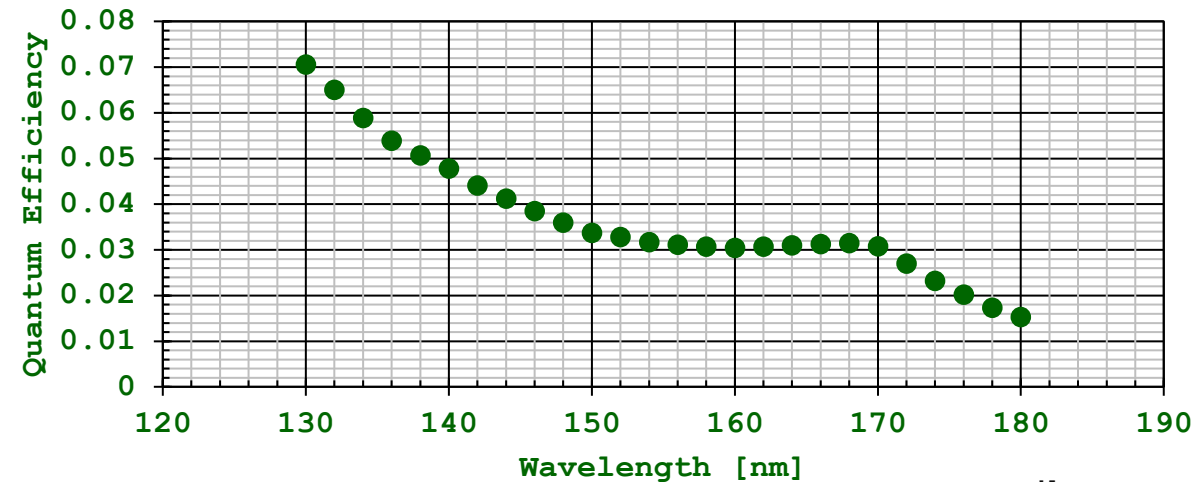


- Reference Photocurrent CsI PMT
- Photocurrent on the substrate

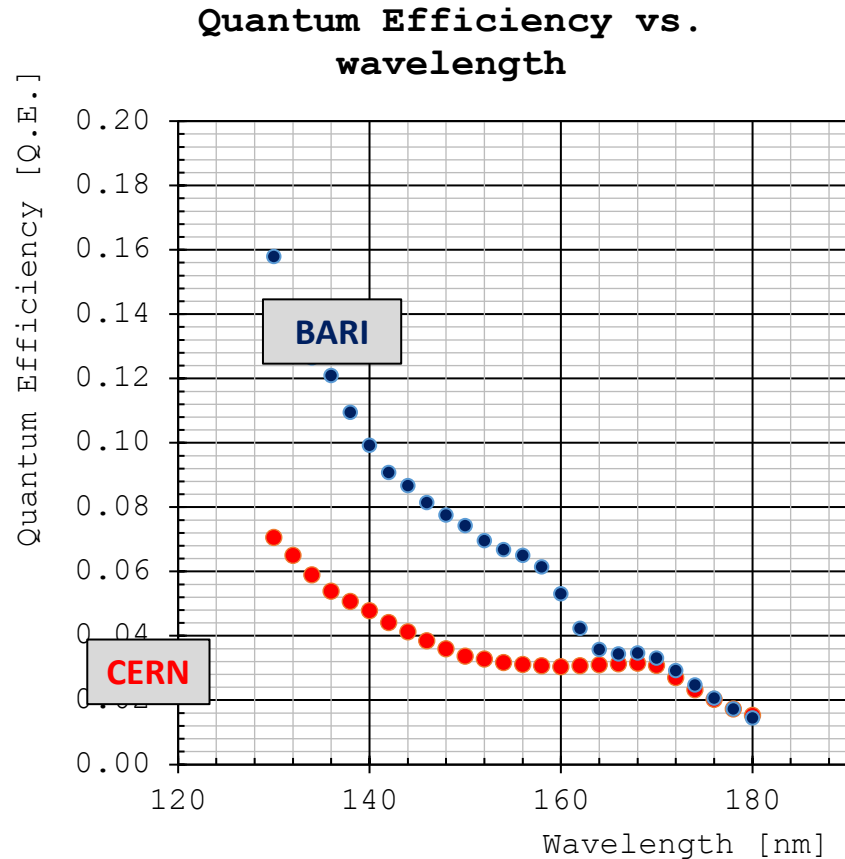
ET Enterprise Calibration for PM 9403 [S.N. 88]



Quantum Efficiency vs. wavelength

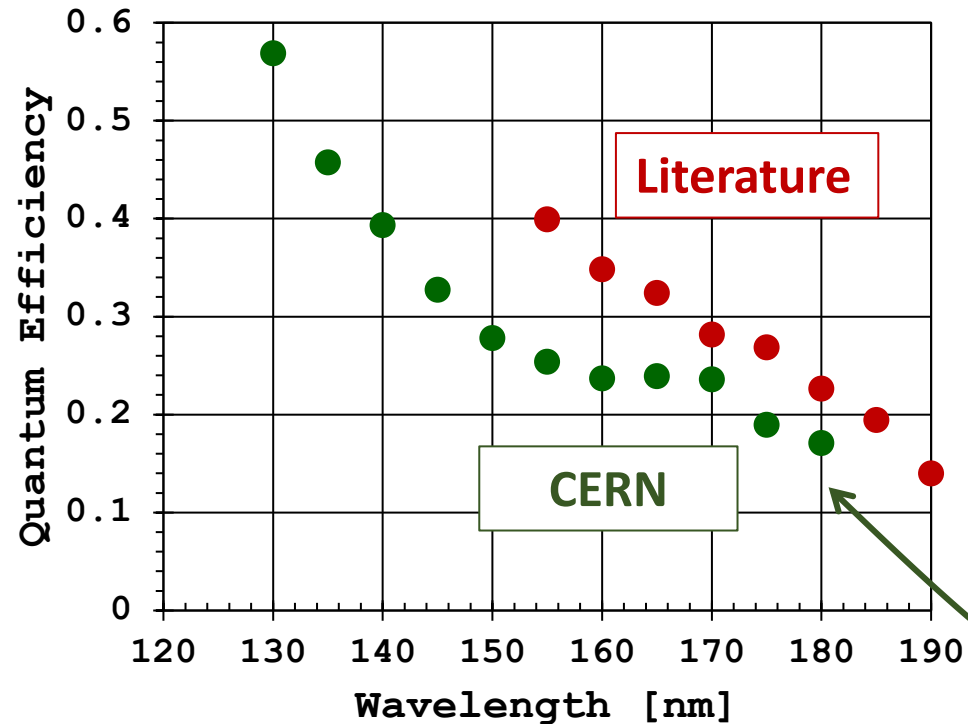


COMPARISON OF CERN RESULTS WITH BARI AND LITERATURE



- QE PCB7 [50 Shots] CERN
- QE PCB7 [50 Shots] Bari

Comparison of CsI QE

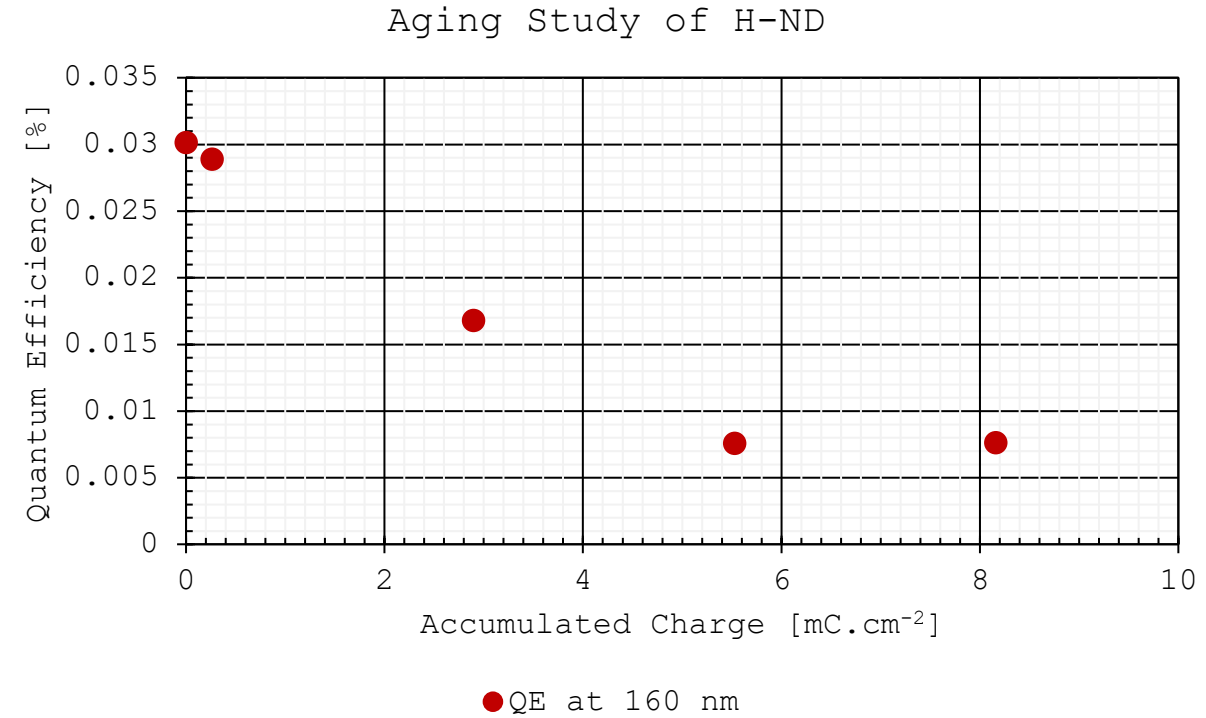
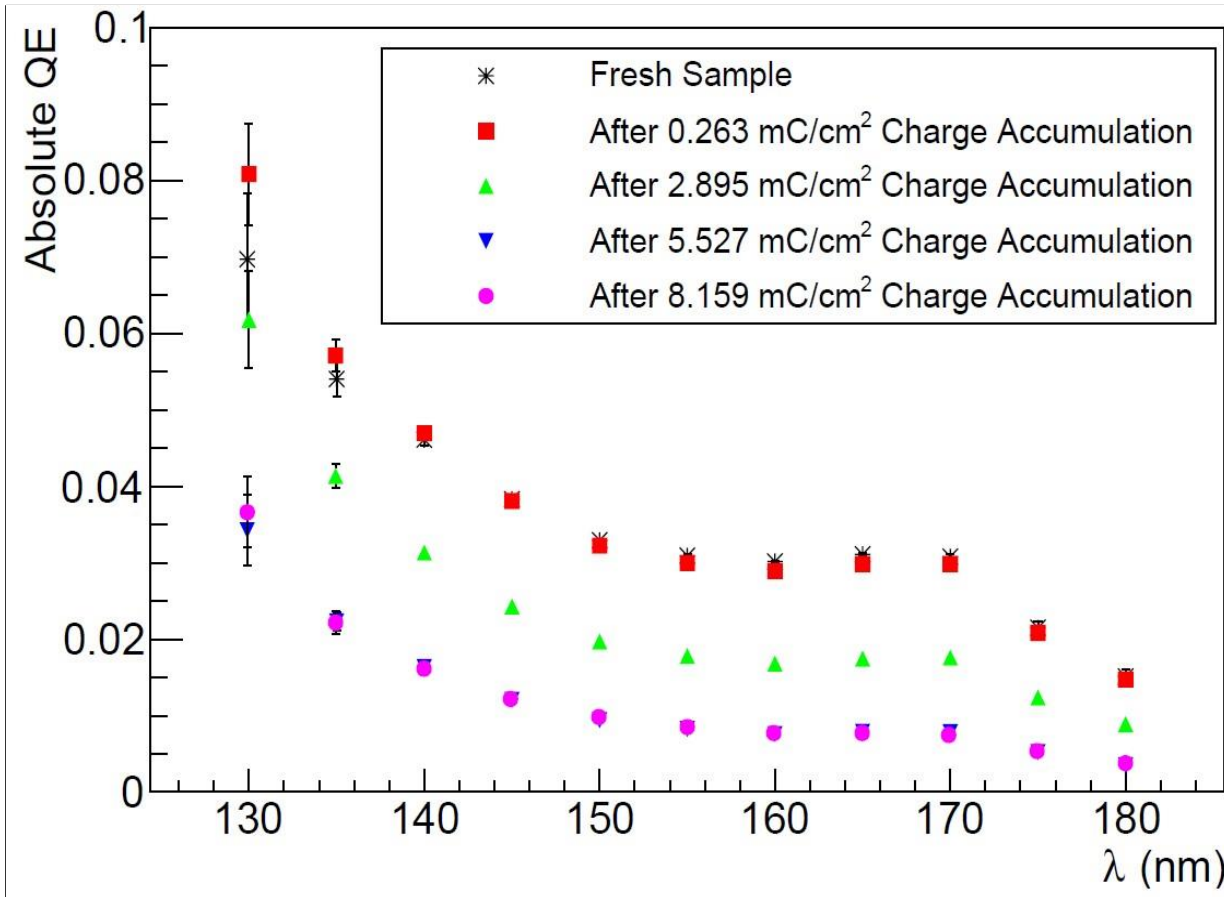


CsI coated at CERN and measured with ASSET setup

- CsI_NIMA_525_2004_173
- CsI_300nm_Fresh

ASSET is in building up state, comparative analyses are useful

AGEING STUDY WITH X-RAY IRRADIATION OF H-ND



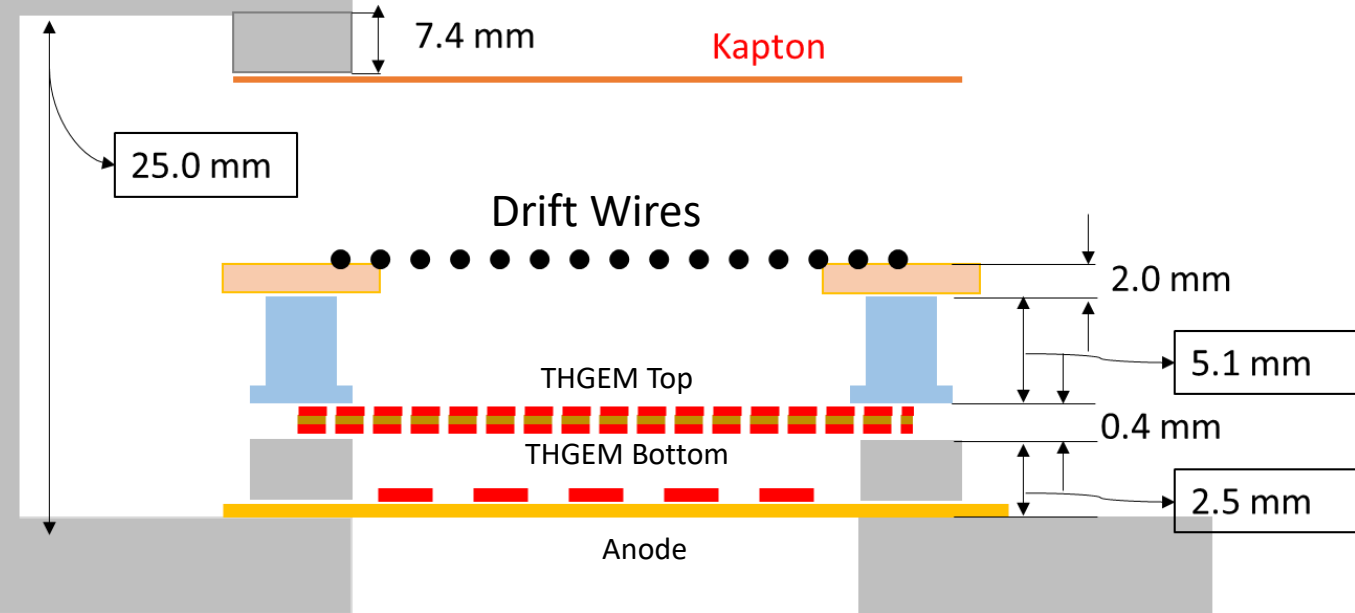
Thickness (t) = 0.4 mm

Diameter (d) = 0.4 mm

Pitch (p) = 0.8 mm

THGEM parameters

Prototype used for measurements (Schematic)



- THGEMs are standard Printed Circuit Boards (PCBs) with holes produced by mechanical drilling.
- Like in GEMs, in the presence of a correct electrical bias and in a proper gas mixture, each hole acts as an electron multiplier.
- The signal generated by the gas multiplication is collected at the anode.
- The geometrical parameters of our THGEMs are: hole diameter (d) = 0.4 mm; hole pitch (p) = 0.8 mm; thickness of the fiberglass (t) = 0.4 mm; and rim around holes < 5 μm .

- For measurements the gas mixture used is: $\text{Ar}:\text{CH}_4$ 50:50
- CAEN N1471H HV PS has been used.
- CREMAT CR-110 Preamplifier with CREMAT CR-150 r5 evaluation board has been used to read the signal from the detector.
- Ortec 672 Spectroscopy amplifier with AMPTEK MCA 8000A has been used for processing the signal and for saving the data.

WHAT WE DID SO FAR

- > We coated few old 30 X 30 mm^2 prototypes and as some of them showing pathologies we produced 25 new prototypes with COMPASS standard [$\emptyset=0.4$ mm; $t=0.4$ mm; $p=0.8$ mm; rim <5 μm].
- > After postproduction they are characterized in Trieste LAB.
- > To be sure we bring a small setup in Bari and characterized them before and after coating.
- > First results are already presented in RICH 2018 and MPGD 2019 as a poster. RICH-2018 Proceeding is Published in NIMA_952_2020_161967.
- > A very brief overview in next slide

THGEM CHARACTERIZATION IN BARI

> THGEM used: THGEM IX [d = 0.4 mm; t = 0.4 mm; p = 0.8 mm; RIM < 5 μm];

> Gas Mixture: Ar:CH₄ 50:50.

> CAEN N1471H HV PS

> Voltage Configuration: Drift = 2520 V; Top = 2020 V; Bottom = 500 V;

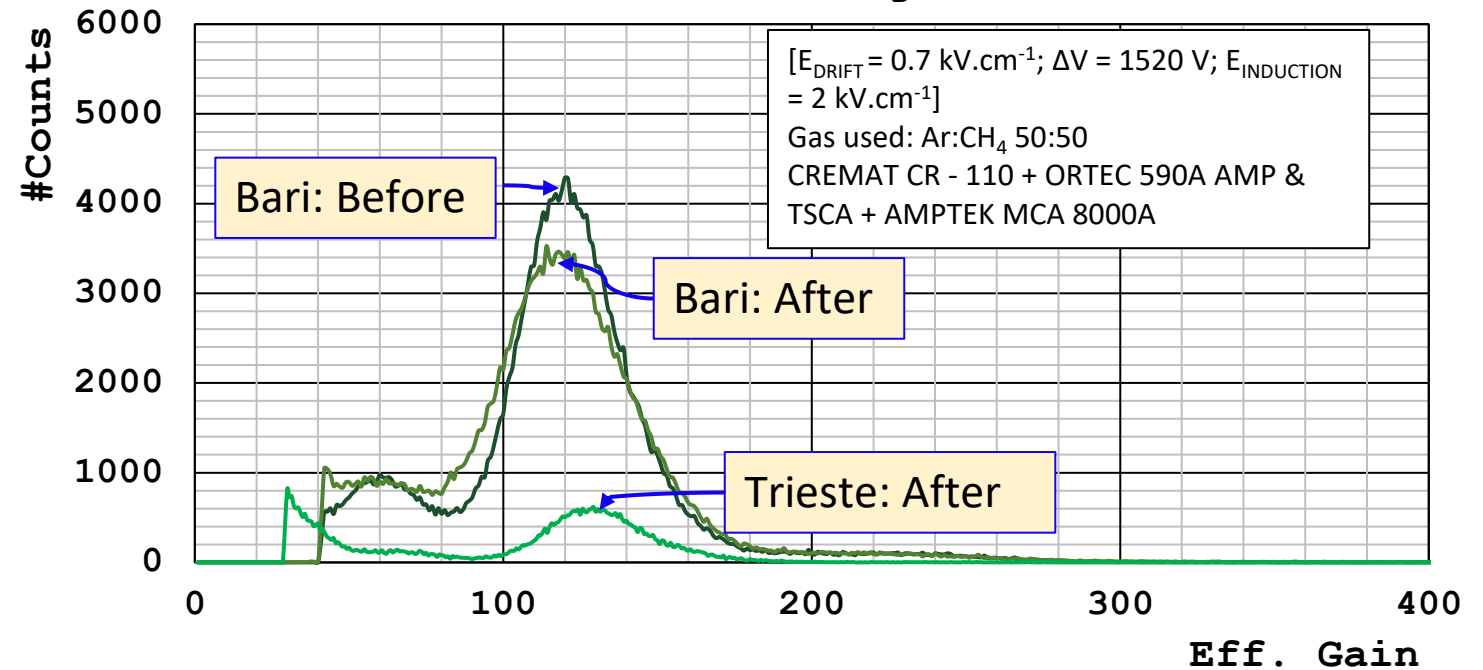
> 55Fe X-Ray source.

> Cremat CR-110 Preamp + ORTEC 590A Amplifier + AMPTEK MCA 8000A.

> Calc. Eff. Gain ~ 122

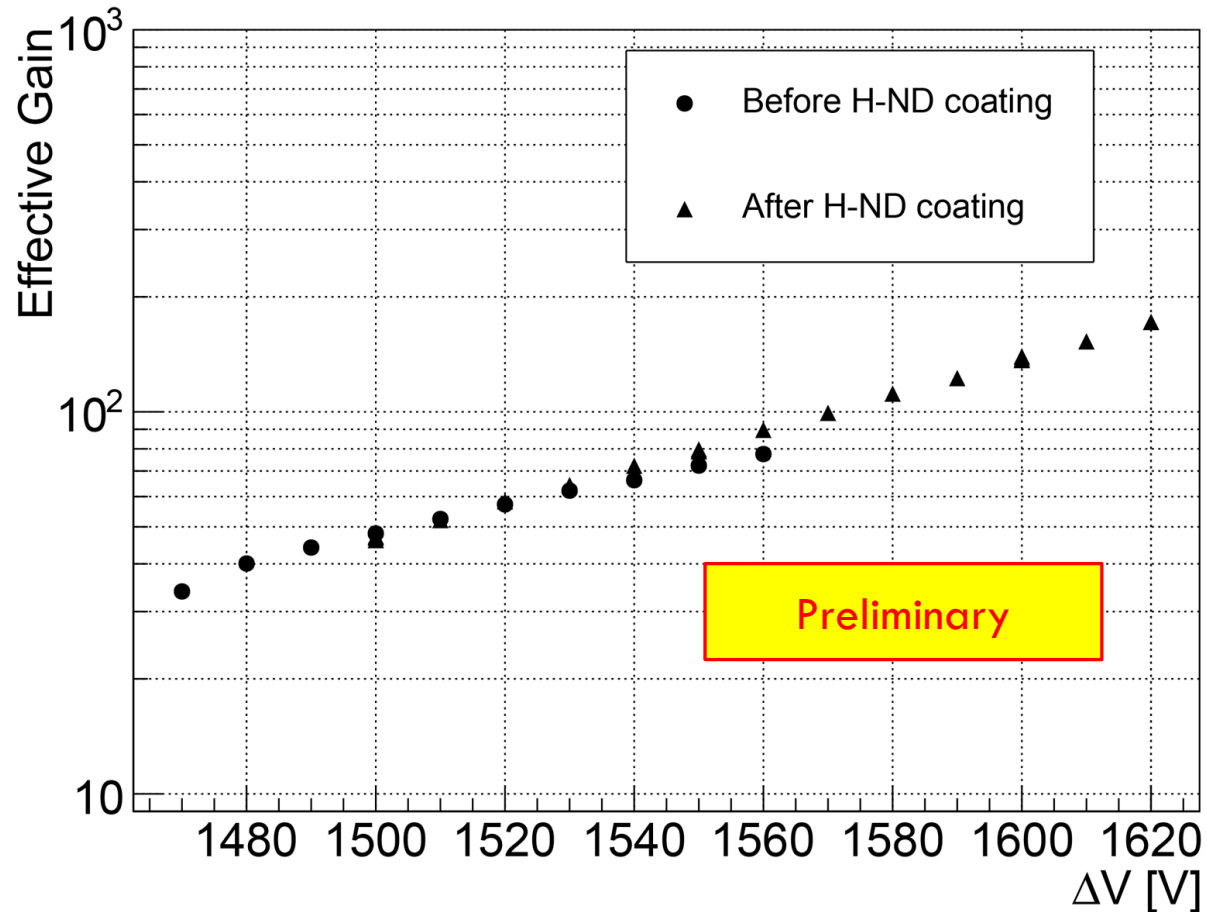
> Heat treatment after coating introduced (24 h at 120° C): W/O treatment THGEM does not stand HV

Spectra of 55Fe Source with THGEM VIII before and after coating with H-ND



THGEMS WITH H-ND

THGEM effective gain vs. bias voltage



> Gas Mixture: Ar:CH₄ 50:50

> ⁵⁵Fe X-Ray source.

> Cremat CR-110 Preamp + ORTEC 590A Amplifier + AMPTEK MCA 8000A.

> After coating and after heat treatment THGEMs sustain higher bias voltage

FUTURE STEPS

- > QE measurement with fresh H-ND
- > Exploration of different powders
- > Systematic characterization of THGEMs
- > H-ND coated “hybrid prototype” (THGEMs + MM)



CONCLUSIONS

Preliminary results are encouraging:

- > H-ND shows high QE (not as high as expected, though)
- > H-ND shows robustness to ion bombardment
- > Coated THGEM perform nicely thanks to heat treatment

Both BARI and CERN setup useful:

- **BARI**: (H-)ND photocathodes can be produced, mature setup for absolute QE measurement
- **CERN**: flexible setup where measurements like radiation damage profile scanning are possible

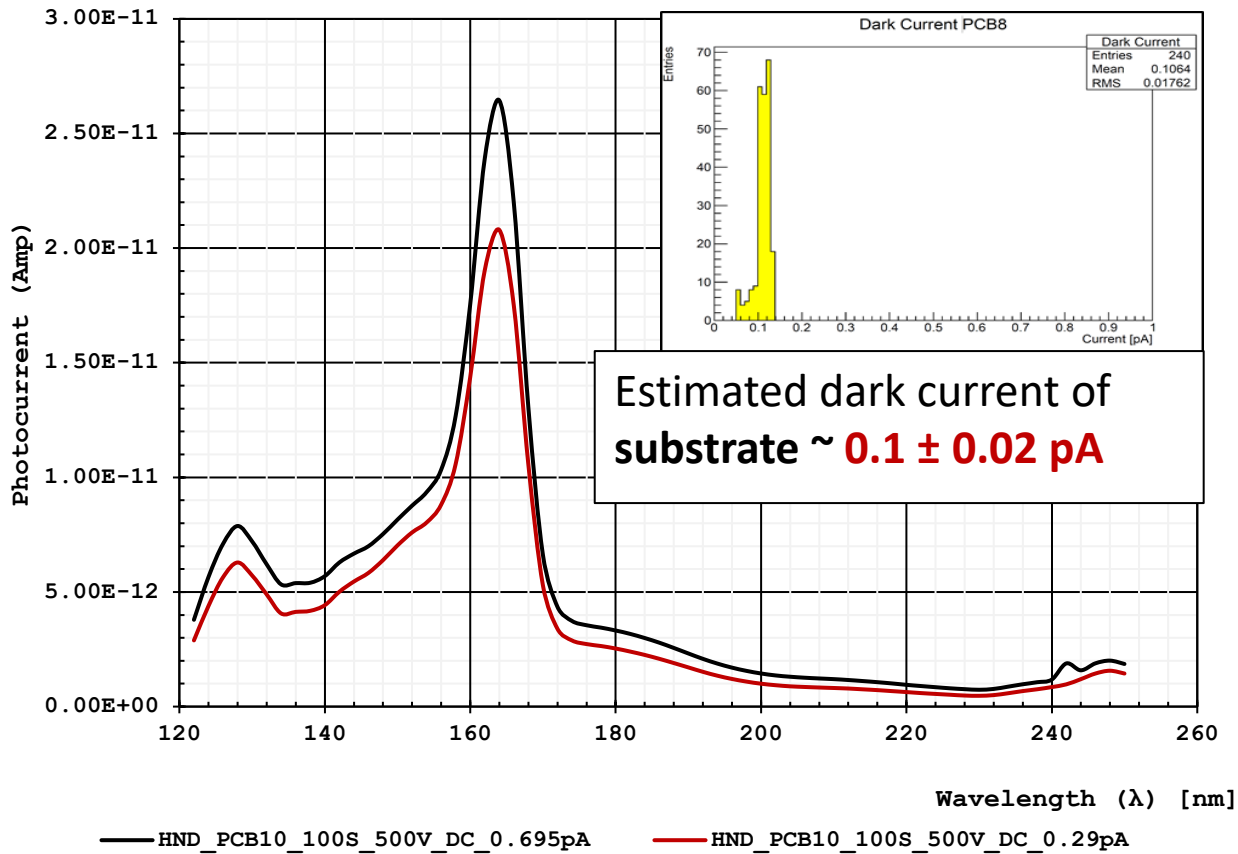
BIBLIOGRAPHY

- > L. Velardi et al., Appl. Phys. Lett. 108, 083503 (2016);
- > Brunbauer F.M. et al., JINST, 15 (2020) C09052;
- > Chatterjee C. et al., Nucl. Instrum. Methods Phys. Res. A, 952(2020) 161967;
- > Triloki, “Preliminary results of ND Photocathode coupled to THGEMs”, presentation at RD51 Mini-week, 10-13 February 2020, <https://indico.cern.ch/event/872501>;

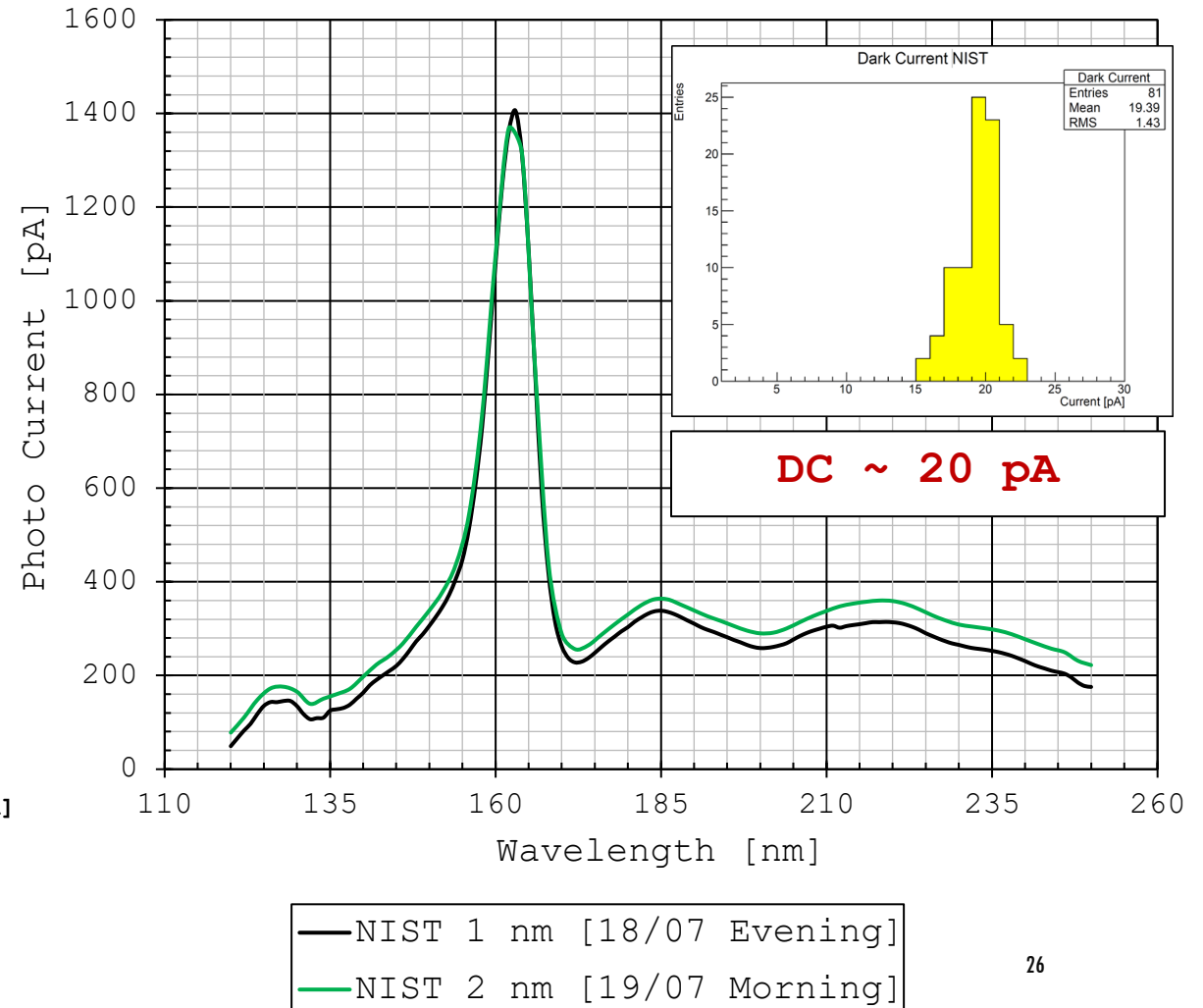
BACKUP SLIDES

NOISE AND REPRODUCIBILITY (BARI SETUP)

Photocurrent_HND_Vacuum

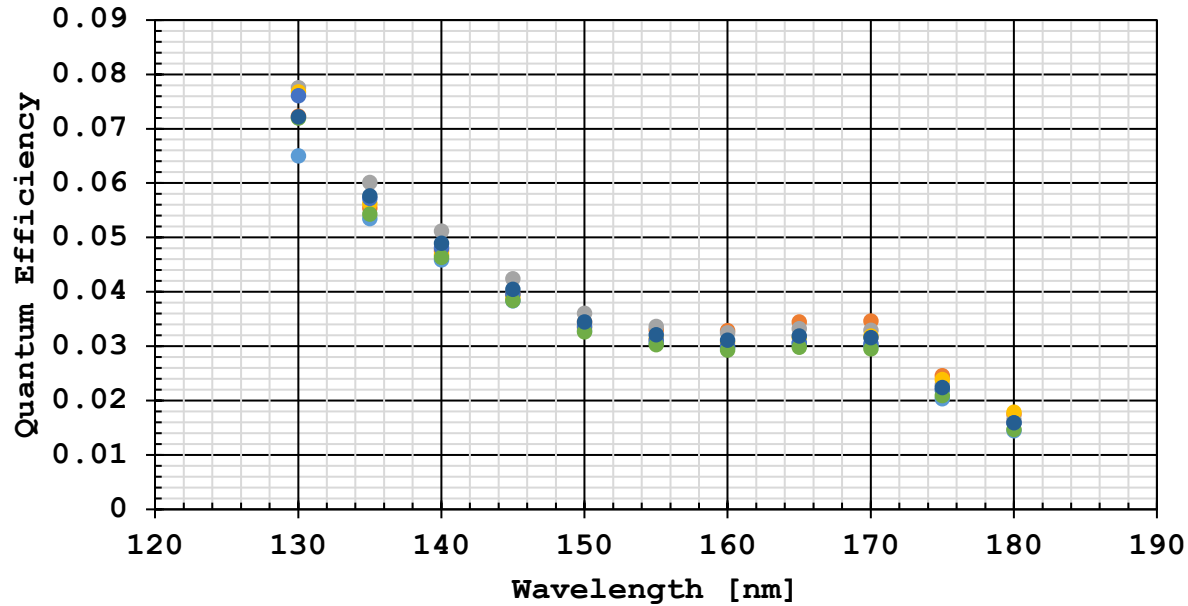


NIST photo current vs. wavelength



REPRODUCIBILITY (CERN SETUP)

PCB7 [50 Shots] QE vs. Wavelength



- 12-12-19 13.04 ● 13-12-19 10.31 ● 13-12-19 11.37
- 13-12-19 18.19 ● 13-12-19 19.34 ● 14-12-19 11.17
- 14-12-19 12.04

Standard Deviation of the repeated measurements of PCB7 [50 Shots]

